



KL2G-1010-SiO₂/Si

KL2G-1010-SiO₂/Si is a single 10mmx10mm bilayer of CVD graphene film, on silicon. Both layers of graphene were grown on copper foil, and transferred individually by wet film transfer to the silicon substrate.

Graphene Film

Growth Method	CVD synthesis
Transfer Method	Clean transfer method
Quality Control	Optical Microscopy & Raman checked
Appearance (Color)	Transparent
Transparency	>97%
Appearance (Form)	Film
Coverage	>95%
Number of graphene layers	2
Thickness (theoretical)	0.345 nm
Field Effect Mobility on SiO ₂ /Si	2,000 cm ² /V·s
Hall Effect Mobility on SiO ₂ /Si	4,000 cm ² /V·s
Sheet Resistance on SiO ₂ /Si (Van der Pauw)	190±30 Ohms/sq. (1cm x 1cm)
Grain size	Up to 10 μm

Substrate

	SiO₂/Si
Type/Dopant	P/Bor
Orientation	<100>
Growth Method	CZ
Resistivity	<0.005 ohm cm
Thickness	525 +/- 20 μm
Front Surface	Polished
Back Surface	Etched
Flats	2 SEMI

Optical Microscopy

